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AF #
Duplicate
501.39149X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: NAKAMURA et al.
Serial No.: 09/708,450
Filed: November 9, 2000
For: A SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
AND THE METHOD THEREOF
Group: 2811
Examiner: D. Owens

CONFIRMATION FILING OF APRIL 21 AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

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TECHNOLOGY CENTER 28000
April 29, 2003

Sir:

Applicants filed a responsive Amendment after Final Rejection and Petition for One Month Extension of Time on April 21, 2003. A copy of the U.S. post card showing the filing of this Amendment is attached. Additionally, hereto is a copy of the April 21 Amendment after Final Rejection and Petition for Extension of Time.

These copies are merely being filed as confirmation copies of the previous filed documents. That is, these documents are identical to the previously filed

documents. While these documents were timely filed on April 21, 2003, if any extension of time fee is necessary in order to enter these April 21 documents, then applicants petition for an extension of time under 37 C.F.R. §1.136. Please charge any fee in connection with an extension of time to account 01-2135 (referencing case no. 501.39149X00).

Respectfully submitted,

David C. Oren
Registration No. 38,694
ANTONELLI, TERRY, STOUT & KRAUS, LLP

DCO/pay

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- A circular stamp from the Office of Intellectual Property (OIP). The text "OIP" is at the top, "JC17" is at the top right, "APR 21 2003" is in the center, and "PATENT & TRADEMARK OFFICE" is at the bottom.



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AMENDMENT AFTER FINAL REJECTION

BOX AF

Commissioner for Patents
Washington, D.C. 20231

April 21, 2003

Sir:

In response to the Office Action dated November 20, 2002, please amend the above-identified application as follows.

IN THE CLAIMS:

Please cancel claims 23 and 27 without prejudice or disclaimer.

Please amend claims 20-22, 24-26 and 28-34 as follows:

20. (Twice Amended) A method of producing a semiconductor integrated circuit device comprising the steps of:

(a) forming bit lines and a first layer wiring over MISFET on a main plane of a semiconductor substrate through a first inter-layer insulating film, forming a second inter-layer insulating film and an electrode-forming insulating film, and etching holes in said electrode-forming insulating film;